High Voltage Transistors

NPN Silicon

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



Characteristic	Symbol	Value	Unit
Collector - Emitter Voltage MMBTA42, SMMBTA42 MMBTA43	V _{CEO}	300 200	Vdc
Collector - Base Voltage MMBTA42, SMMBTA42 MMBTA43	V _{CBO}	300 200	Vdc
Emitter-Base Voltage MMBTA42, SMMBTA42 MMBTA43	V _{EBO}	6.0 6.0	Vdc
Collector Current - Continuous	I _C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

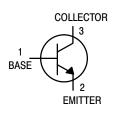
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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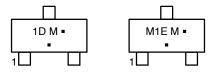
http://onsemi.com





SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAMS



1D = MMBTA42LT, SMMBTA42L

M1E = MMBTA43LT
M = Date Code*

Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (Note 3) (I _C = 1.0 mAdc, I _B = 0)	MMBTA42, SMMBTA42 MMBTA43	V _{(BR)CEO}	300 200	_ _	Vdc	
Collector – Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)	MMBTA42, SMMBTA42 MMBTA43	V _(BR) CBO	300 200	- -	Vdc	
Emitter – Base Breakdown Voltage ($I_E = 100 \mu Adc, I_C = 0$)		V _{(BR)EBO}	6.0	-	Vdc	
Collector Cutoff Current $(V_{CB} = 200 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 160 \text{ Vdc}, I_E = 0)$	MMBTA42, SMMBTA42 MMBTA43	Ісво	- -	0.1 0.1	μAdc	
Emitter Cutoff Current $(V_{EB} = 6.0 \text{ Vdc}, I_C = 0)$ $(V_{EB} = 4.0 \text{ Vdc}, I_C = 0)$	MMBTA42, SMMBTA42 MMBTA43	I _{EBO}	- -	0.1 0.1	μAdc	
ON CHARACTERISTICS (Note 3)						
DC Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$)	Both Types Both Types	h _{FE}	25 40	- -	-	
$(I_C = 30 \text{ mAdc}, V_{CE} = 10 \text{ Vdc})$	MMBTA42, SMMBTA42 MMBTA43		40 40	- -		
Collector - Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 2.0 mAdc)	MMBTA42, SMMBTA42 MMBTA43	V _{CE(sat)}	- -	0.5 0.5	Vdc	
Base–Emitter Saturation Voltage ($I_C = 20 \text{ mAdc}$, $I_B = 2.0 \text{ mAdc}$)		V _{BE(sat)}	_	0.9	Vdc	
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)		f _T	50	_	MHz	
Collector-Base Capacitance (V _{CB} = 20 Vdc, I _E = 0, f = 1.0 MHz)	MMBTA42, SMMBTA42 MMBTA43	C _{cb}	- -	3.0 4.0	pF	

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

TYPICAL CHARACTERISTICS

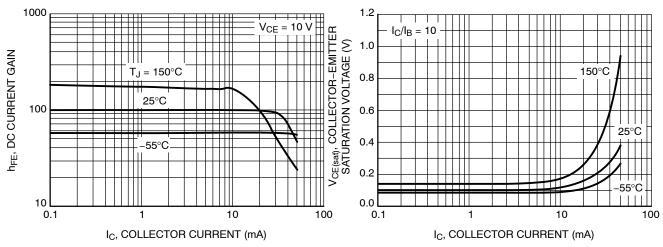


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

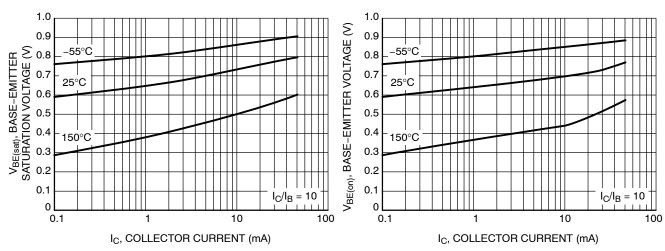


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

Figure 4. Base-Emitter On Voltage vs. Collector Current

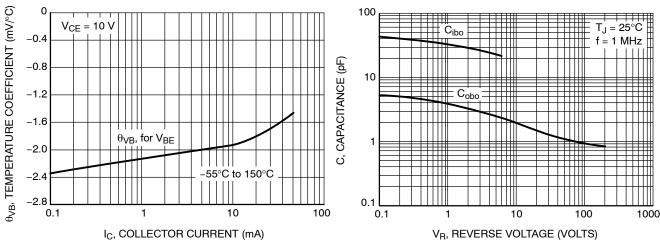


Figure 5. Base-Emitter Temperature Coefficient

Figure 6. Capacitance

TYPICAL CHARACTERISTICS

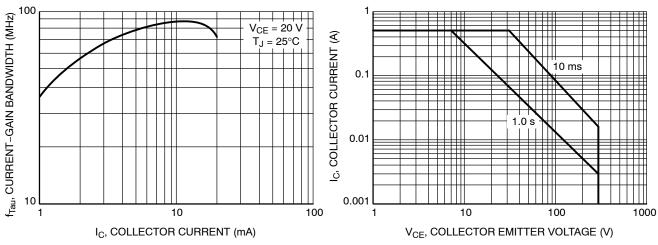


Figure 7. Current-Gain — Bandwidth Product

Figure 8. Safe Operating Area

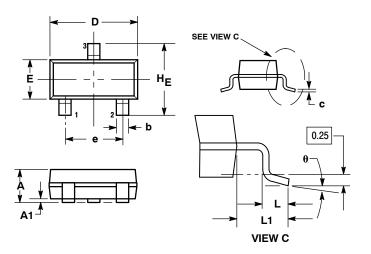
ORDERING INFORMATION

Device Order Number	Package Type	Shipping [†]	
MMBTA42LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel	
SMMBTA42LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel	
MMBTA42LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel	
SMMBTA42LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel	
MMBTA43LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

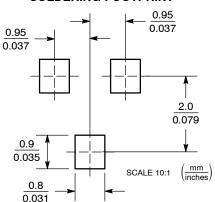
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6:

PIN 1. BASE

EMITTER COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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